

8550 (1.5A)

PNP Silicon Epitaxial Planar Transistor

for switching and amplifier applications.
Especially suitable for AF-driver stages
and low power output stages.



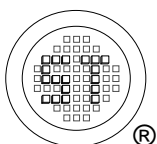
1. Emitter 2. Base 3. Collector
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|---------------------------|------------|---------------|------------------|
| Collector Base Voltage | $-V_{CBO}$ | 40 | V |
| Collector Emitter Voltage | $-V_{CEO}$ | 25 | V |
| Emitter Base Voltage | $-V_{EBO}$ | 6 | V |
| Collector Current | $-I_C$ | 1.5 | A |
| Power Dissipation | P_{tot} | 1 | W |
| Junction Temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{Stg} | - 55 to + 150 | $^\circ\text{C}$ |

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

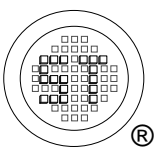
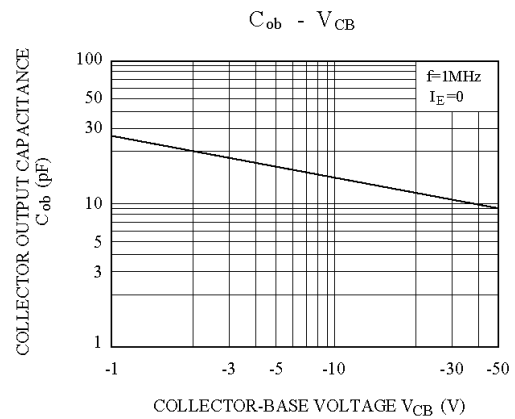
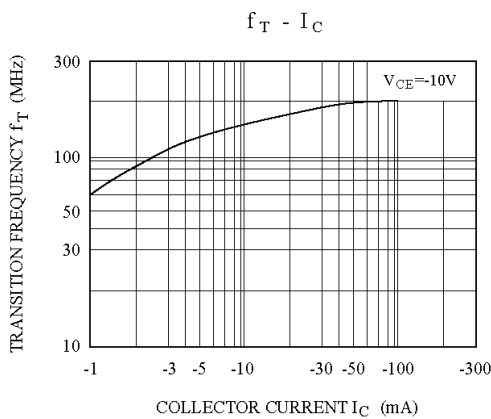
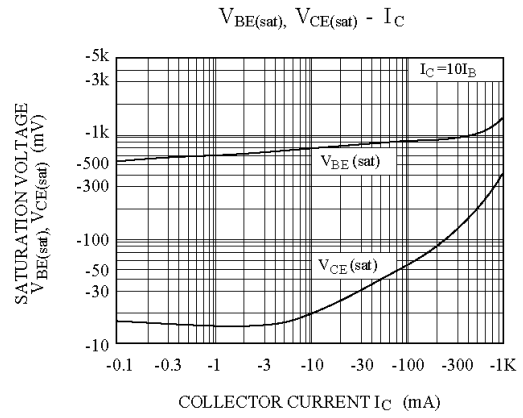
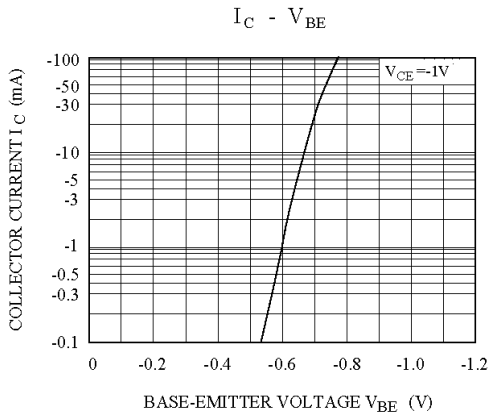
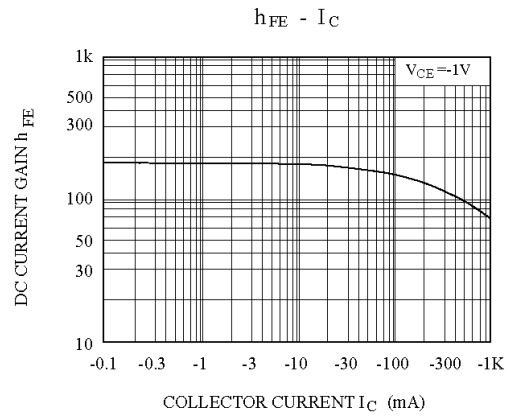
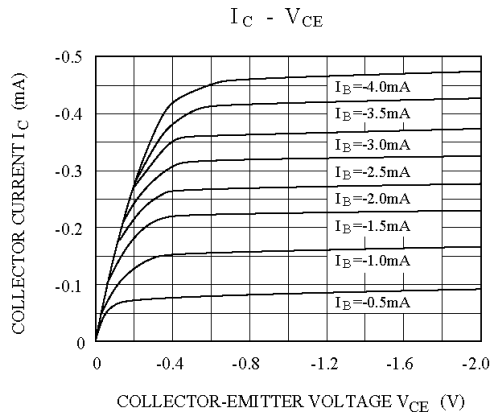
| Parameter | Symbol | Min. | Typ. | Max. | Unit |
|---|------------------------------|----------|------|------|------|
| DC Current Gain at $-V_{CE} = 1\text{ V}$, $-I_C = 5\text{ mA}$ at $-V_{CE} = 1\text{ V}$, $-I_C = 100\text{ mA}$ at $-V_{CE} = 1\text{ V}$, $-I_C = 800\text{ mA}$ | Current Gain Group C D | h_{FE} | 45 | - | - |
| | | h_{FE} | 120 | - | 200 |
| | | h_{FE} | 160 | - | 300 |
| | | h_{FE} | 40 | - | - |
| Collector Base Cutoff Current at $-V_{CB} = 35\text{ V}$ | $-I_{CBO}$ | - | - | 100 | nA |
| Emitter Base Cutoff Current at $-V_{BE} = 6\text{ V}$ | $-I_{EBO}$ | - | - | 100 | nA |
| Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$ | $-V_{(BR)CBO}$ | 40 | - | - | V |
| Collector Emitter Breakdown Voltage at $-I_C = 2\text{ mA}$ | $-V_{(BR)CEO}$ | 25 | - | - | V |
| Emitter Base Breakdown Voltage at $-I_E = 100\text{ }\mu\text{A}$ | $-V_{(BR)EBO}$ | 6 | - | - | V |
| Collector Emitter Saturation Voltage at $-I_C = 800\text{ mA}$, $-I_B = 80\text{ mA}$ | $-V_{CE(sat)}$ | - | - | 0.5 | V |
| Base Emitter Saturation Voltage at $-I_C = 800\text{ mA}$, $-I_B = 80\text{ mA}$ | $-V_{BE(sat)}$ | - | - | 1.2 | V |
| Base Emitter Voltage at $-I_C = 10\text{ mA}$, $-V_{CE} = 1\text{ V}$ | $-V_{BE}$ | - | - | 1 | V |
| Gain Bandwidth Product at $-V_{CE} = 10\text{ V}$, $-I_C = 50\text{ mA}$ | f_T | 120 | - | - | MHz |
| Collector Base Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$ | C_{ob} | - | 15 | - | pF |



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ISO/TS 16949 : 2009
Certificate No. 16073009

ISO14001 : 2004
Certificate No. 7116

ISO 9001 : 2008
Certificate No. 5073410

BS-OHSAS 18001 : 2007
Certificate No. 7116

IECQ QC 080000
Certificate No. PRC-85P4-148-1

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